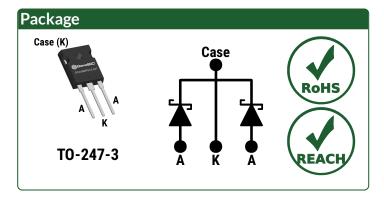
Silicon Carbide Schottky Diode



 V_{RRM} = 1200 V $I_{F(T_C = 161^{\circ}C)}$ = 10 A * Q_C = 54 nC *

Features

- Low V_F for High Temperature Operation
- Enhanced Surge and Avalanche Robustness
- Superior Figure of Merit Qc/IF
- Low Thermal Resistance
- Low Reverse Leakage Current
- Temperature Independent Fast Switching
- Positive Temperature Coefficient of V_F
- High dV/dt Ruggedness



Advantages

- Improved System Efficiency
- High System Reliability
- Optimal Price Performance
- Reduced Cooling Requirements
- Increased System Power Density
- Zero Reverse Recovery Current
- Easy to Parallel without Thermal Runaway
- Enables Extremely Fast Switching

Applications

- Power Factor Correction (PFC)
- Solar Inverters
- Electric Vehicles
- High Frequency Converters
- Battery Chargers
- AC/DC Power Supplies
- Anti-Parallel / Free-Wheeling Diode
- LED and HID Lighting

Absolute Maximum Ratings (At T _C = 25°C Unless Otherwise Stated)										
Parameter	Symbol	Conditions Values		Unit	Note					
Repetitive Peak Reverse Voltage (Per Leg)	V_{RRM}		1200	٧						
Continuous Forward Current (Per Leg / Per Device)	lF	$T_C = 100^{\circ}C, D = 1$	14 / 28							
		$T_C = 135^{\circ}C, D = 1$	9 / 18	Α	Fig. 4					
		$T_C = 161^{\circ}C, D = 1$	5 / 10							
Non-Repetitive Peak Forward Surge Current, Half Sine Wave (Per Leg)	Iғ,sм	T_C = 25°C, t_P = 10 ms	50	٨						
		T_C = 150°C, t_P = 10 ms	40	Α						
Repetitive Peak Forward Surge Current, Half Sine Wave	I _{F,RM}	T_C = 25°C, t_P = 10 ms	30	Α						
(Per Leg)		T_C = 150°C, t_P = 10 ms	21	А						
Non-Repetitive Peak Forward Surge Current (Per Leg)	I _{F,MAX}	T_C = 25°C, t_P = 10 μ s	250	Α						
i ² t Value (Per Leg)	∫i²dt	T_C = 25°C, t_P = 10 ms	12	A ² s						
Non-Repetitive Avalanche Energy (Per Leg)	Eas	$L = 7.2 \text{ mH}, I_{AS} = 5 \text{ A}$	90	mJ						
Diode Ruggedness (Per Leg)	dV/dt	$V_R = 0 \sim 960 \text{ V}$	200	V/ns						
Power Dissipation (Per Leg / Per Device)	P _{TOT}	T _C = 25°C	104 / 208	W	Fig. 3					
Operating and Storage Temperature	Tj, Tstg		-55 to 175	°C						

^{*} Per Device





Electrical Characteristics (Per Leg) Values **Parameter Symbol Conditions** Unit Note Min. Тур. Max. $I_F = 5 A$, $T_i = 25$ °C 1.5 1.8 ٧ Diode Forward Voltage V_{F} Fig. 1 $I_F = 5 A$, $T_j = 175$ °C 1.9 $V_R = 1200 \text{ V, } T_i = 25^{\circ}\text{C}$ 5 1 **Reverse Current** Fig. 2 I_R μΑ $V_R = 1200 \text{ V}, T_j = 175^{\circ}\text{C}$ 6 $V_R = 400 V$ 18 **Total Capacitive Charge** $Q_{\mathbb{C}}$ nC Fig. 7 $V_R = 800 V$ 27 $I_F \leq I_{F,MAX}$ $dI_F/dt = 200 A/\mu s$ V_R = 400 V Switching Time < 10 ts ns $V_R = 800 V$ $V_R = 1 V$, f = 1MHz305 С **Total Capacitance** рF Fig. 6 V_R = 800 V, f = 1MHz 18

Thermal/Package Characteristics										
Parameter	Symbol	Conditions	Values			- Unit	Note			
		Conditions	Min.	Тур.	Max.	UIIIL	Note			
Thermal Resistance, Junction - Case (Per Leg)	R _{thJC}			1.44		°C/W	Fig. 9			
Weight	W _T			6.1		g				
Mounting Torque	T _M	Screws to Heatsink			1.1	Nm				





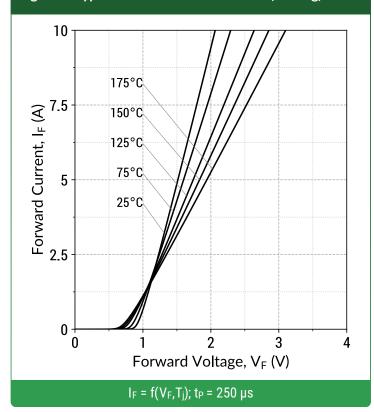


Figure 2: Typical Reverse Characteristics (Per Leg)

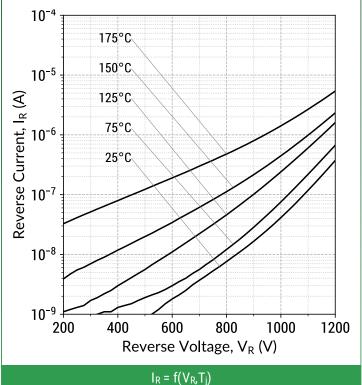


Figure 3: Power Derating Curves (Per Leg)

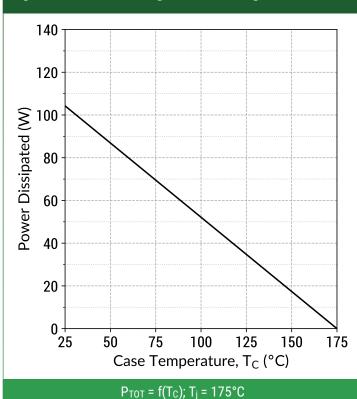


Figure 4: Current Derating Curves (Typical V_F) (Per Leg)

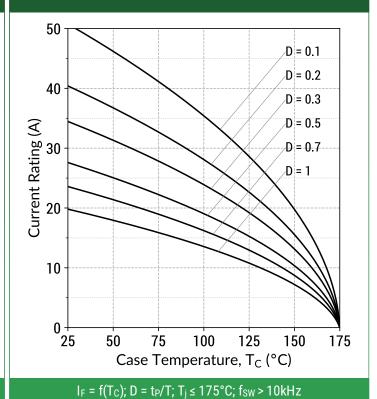
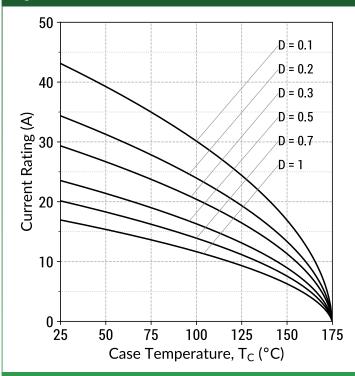


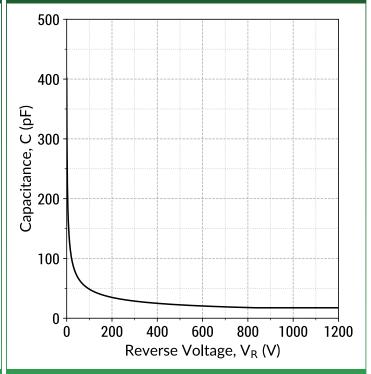


Figure 5: Current Derating Curves (Maximum V_F) (Per Leg)



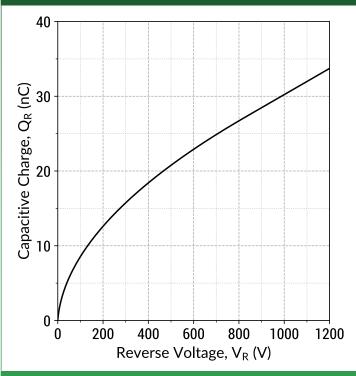
 $I_F = f(T_C)$; D = t_P/T ; $T_j \le 175$ °C; $f_{SW} > 10$ kHz

Figure 6: Typical Junction Capacitance vs Reverse Voltage Characteristics (Per Leg)



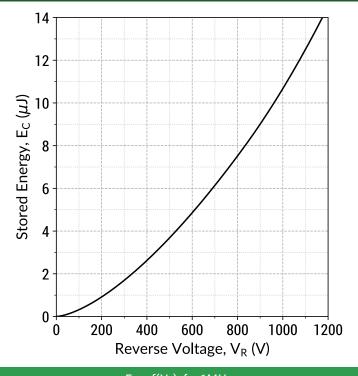
 $C = f(V_R)$; f = 1MHz

Figure 7: Typical Capacitive Charge vs Reverse Voltage Characteristics (Per Leg)



 $Q_C = f(V_R)$; f = 1MHz

Figure 8: Typical Capacitive Energy vs Reverse Voltage Characteristics (Per Leg)



 $E_C = f(V_R)$; f = 1MHz



Figure 9: Transient Thermal Impedance (Per Leg)

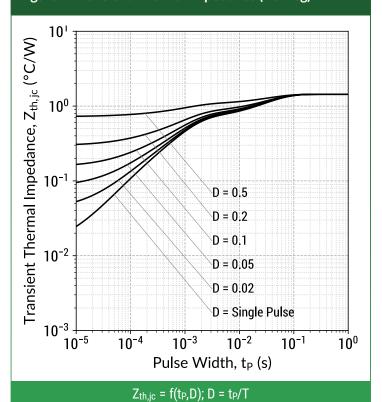
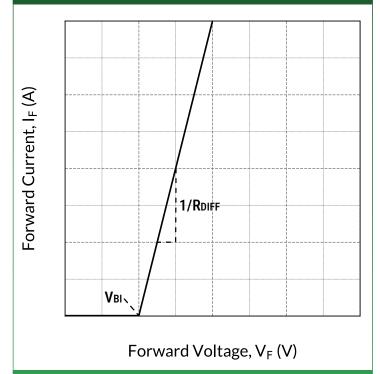


Figure 10: Forward Curve Model (Per Leg)



 $I_F = f(V_F, T_j)$

Forward Curve Model Equation:

 $I_F = (V_F - V_{BI})/R_{DIFF} (A)$

Built-In Voltage (V_{BI}):

$$V_{BI}(T_j) = m \times T_j + n (V)$$

 $m = -0.00123 (V/^{\circ}C)$
 $n = 0.995 (V)$

Differential Resistance (RDIFF):

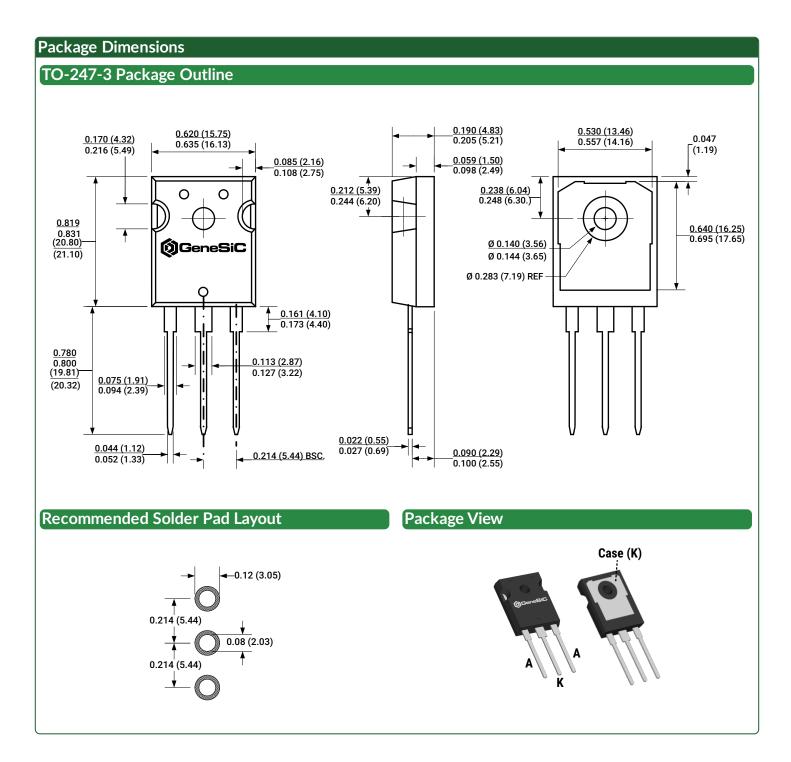
$$R_{DIFF}(T_j) = a \times T_j^2 + b \times T_j + c (\Omega)$$

 $a = 2.38e-06 (\Omega/^{\circ}C^2)$
 $b = 0.000338 (\Omega/^{\circ}C)$
 $c = 0.1 (\Omega)$

Forward Power Loss Equation:

$$P_{LOSS} = V_{BI}(T_i) \times I_{AVG} + R_{DIFF}(T_i) \times I_{RMS}^2$$





NOTE

- 1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
- 2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.





Compliance

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

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Revision History

Rev 21/Jul: Updated with most recent test data
 Supersedes: Rev 19/Apr, Rev 20/Apr, Rev 20/Aug



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